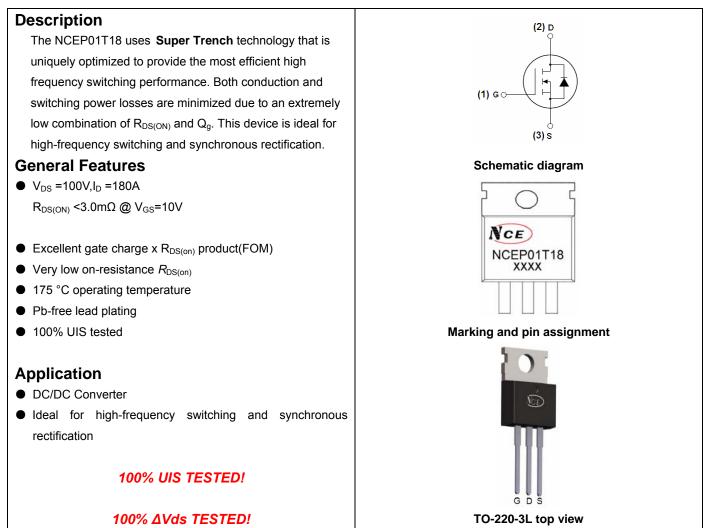


NCE N-Channel Super Trench Power MOSFET



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP01T18	NCEP01T18	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	100	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	180	A
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	128	А
Pulsed Drain Current	I _{DM}	720	A
Maximum Power Dissipation	PD	300	W
Derating factor		2	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1800	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C







Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{0JC}	0.5	°C /W
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Electrical Characteristics (T_C=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	····					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V -		-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	I			•		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	2.5	-	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =100A	-	2.8	3.0	mΩ
Forward Transconductance	g FS	V _{DS} =10V,I _D =50A	40	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	11500	-	PF
Output Capacitance	C _{oss}	V_{DS} =50V, V_{GS} =0V,	-	2480	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	75	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	25	-	nS
Turn-on Rise Time	tr	V _{DD} =50V,I _D =100A	-	75	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =1.6 Ω	-	89	-	nS
Turn-Off Fall Time	t _f		-	29	-	nS
Total Gate Charge	Qg	N/ 50)/1 400A	-	158		nC
Gate-Source Charge	Q _{gs}	V_{DS} =50V,I _D =100A,	-	52		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	29		nC
Drain-Source Diode Characteristics	I			•		
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =180A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	180	А
Reverse Recovery Time	t _{rr}	T_J = 25°C, I_F = I_S	-	75		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	185		nC
						1

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ\!\mathrm{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

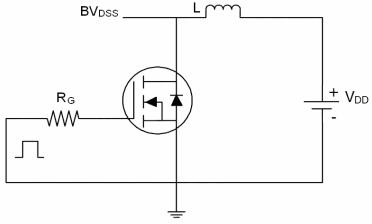


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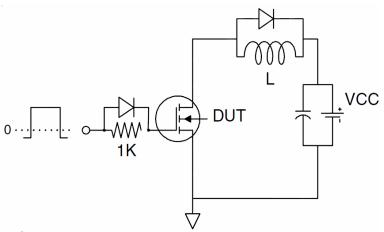




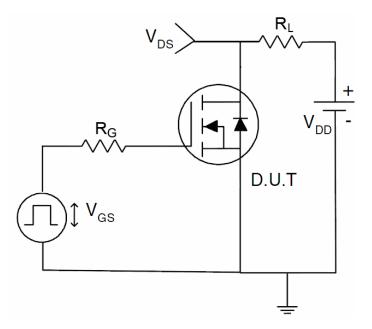
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



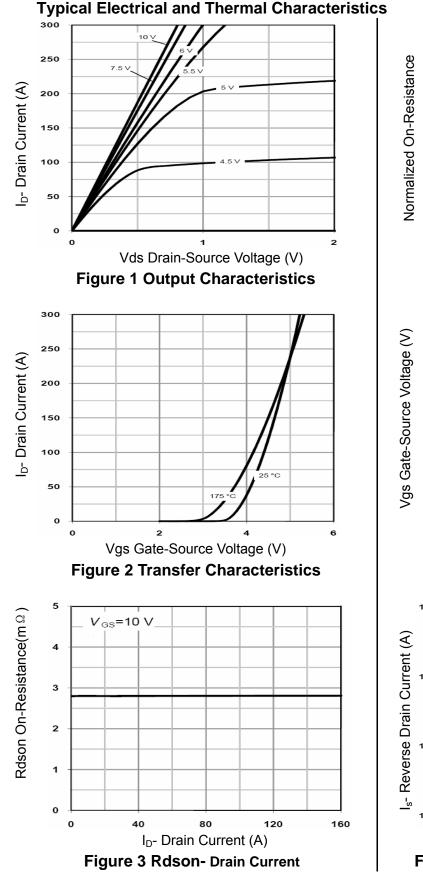
3) Switch Time Test Circuit

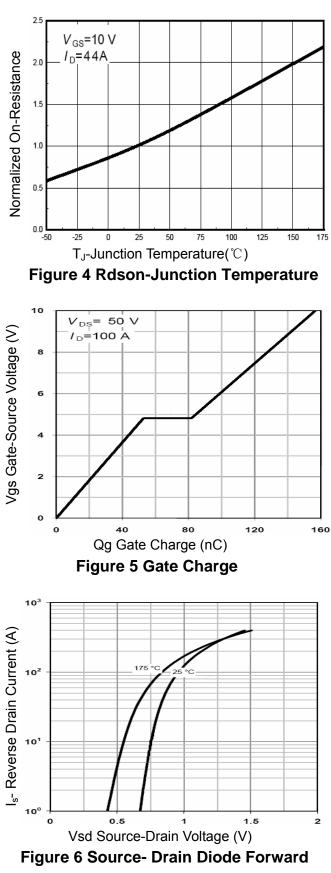




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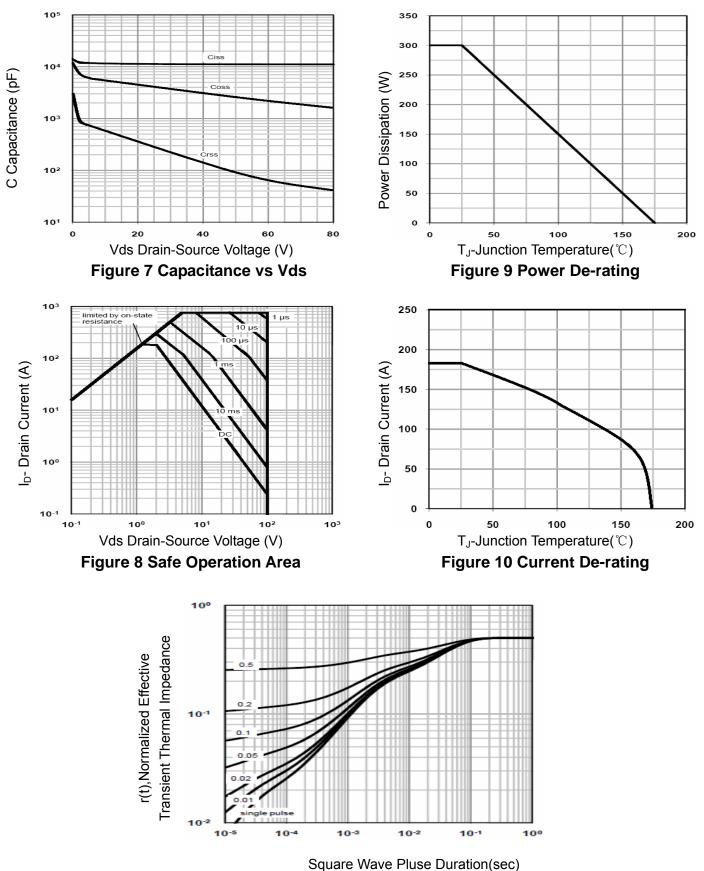


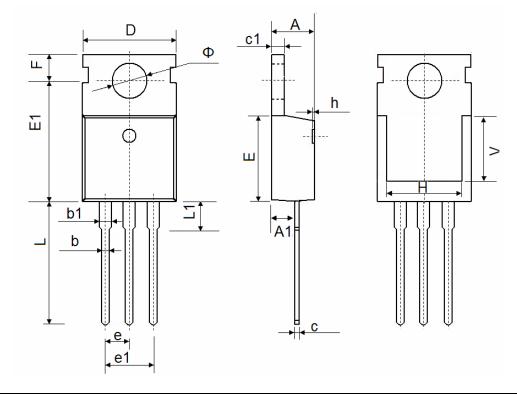
Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
с	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	







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